

SOT223 PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

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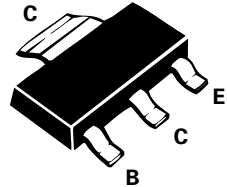
FEATURES

- * For AF drivers and output stages
- * High collector current and Low $V_{CE(sat)}$

COMPLEMENTARY TYPE – BCP68

PARTMARKING DETAIL – BCP69
BCP69 – 25

BCP69



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-25	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-2	A
Continuous Collector Current	I_C	-1	A
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	2	W
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-25			V	$I_C = -10\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-20			V	$I_C = -30mA$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -10\mu A$
Collector Cut-Off Current	I_{CBO}			-100 -10	nA μA	$V_{CB} = -25V$ $V_{CB} = -25V, T_{amb} = 150^{\circ}C$
Emitter Cut-Off Current	I_{EBO}			-10	μA	$V_{EB} = -5V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.5	V	$I_C = -1A, I_B = -100mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.6	-1.0	V V	$I_C = -5A, V_{CE} = -10V^*$ $I_C = -1A, V_{CE} = -1V^*$
Static Forward Current Transfer Ratio	h_{FE} BCP69 BCP69-25	50 63 160	250	400 400		$I_C = -5mA, V_{CE} = -10V^*$ $I_C = -500mA, V_{CE} = -1V^*$ $I_C = -500mA, V_{CE} = -1V^*$
Transition Frequency	f_T		100		MHz	$I_C = -100mA, V_{CE} = -5V,$ $f = 100MHz$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
For typical characteristics graphs see FM1MT549 datasheet.